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hemispherical and hsg

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[\[Abstract\]](#) [\[PDF Full-Text \(368 KB\)\]](#) **IEEE CNF**
**2 An advanced technique for fabricating hemispherical-grained (HSG) storage electrodes**

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*Watanabe, H.; Tatsumi, T.; Ohnishi, S.; Kitajima, H.; Honma, I.; Ikarashi, T.; H.;*  
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